ABSTRACT OF THE DISCLOSURE

A method of reading data in a ferroelectric memory device includes applying a read voltage to a ferroelectric capacitor, and detecting a voltage that reflects an amount of a dynamic change in capacitance of the ferroelectric capacitor to which the read voltage is applied. Since a voltage difference ΔV occurs at a time T between the case where the polarization of a memory cell which has stored first data is not reversed and the case where the polarization of a memory cell which has stored second data is reversed, a read margin increases.